

# HW#3

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- It will be posted soon.
  - Simulation of a pn junction

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# Lecture9:

# Diode models and circuits (1)

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# Forward/reverse

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- A diode shows a strong polarity.
  - Does a resistor have a polarity?
  - In diodes, the following two cases are completely different.
- Forward bias
  - The voltage at the n-type side is higher than the p-type one.



- Reverse bias
  - The voltage at the p-type side is lower than the n-type one.

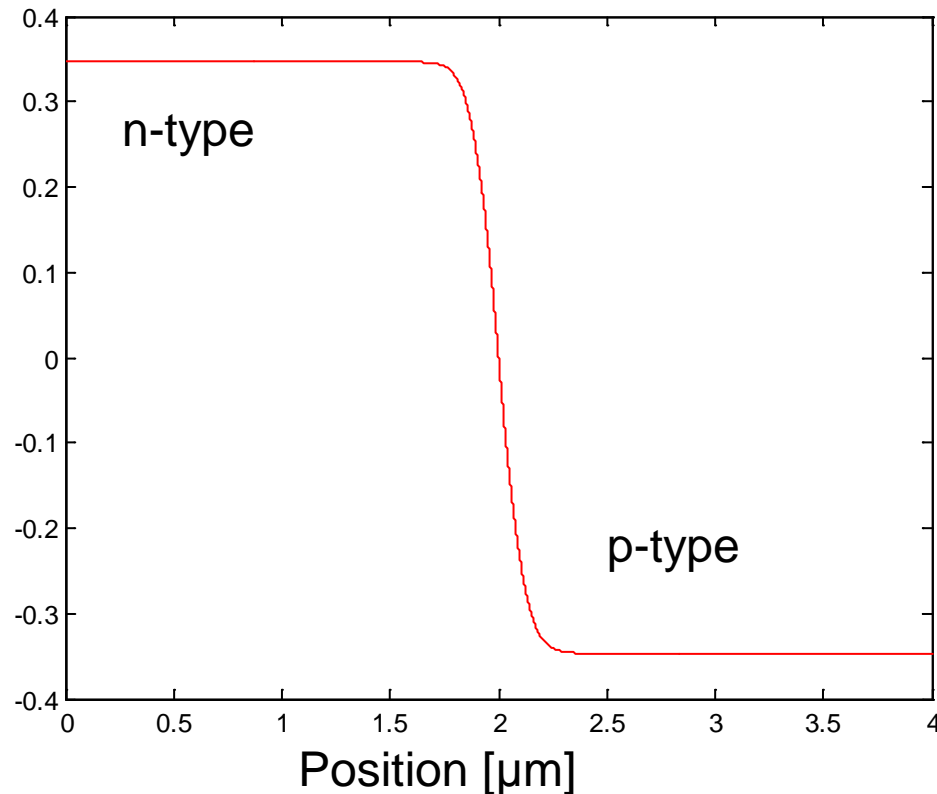


# Reverse bias

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- Electric field
  - Now, the magnitude of the electric becomes larger.

Electric potential [V]



← This is the equilibrium solution. What happens when the n-type region is positively biased?

# Higher electric field?

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- How can the pn junction generate the higher electric field?
  - At equilibrium, how did it generate the built-in electric field?

$$\nabla \cdot \mathbf{D} = \rho$$

- Higher electric field means more space charges!



← Which one can provide nonzero electric field?

- Therefore, the depletion region becomes wider.
  - Even higher potential barrier!

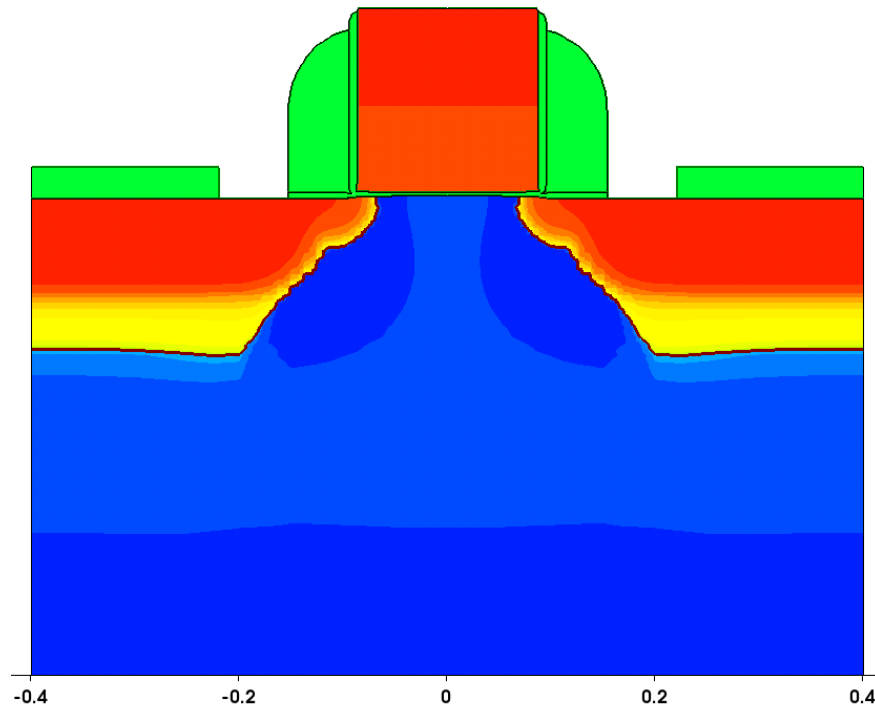
# Variable capacitance

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- Capacitor? Why do we care about it?

$$Q = CV \text{ and } I = C \frac{dV}{dt}$$

- Where can you find capacitance in the following structure?
- Why is it important?



Doping profile of a  
typical planar MOSFET

# Charge

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- Charge stored in a pn junction

$$Q = A \sqrt{2\epsilon_s q \frac{N_A N_D}{N_A + N_D} (V_0 + V_R)}$$

- Then, what is the capacitance at a given value of the reverse bias,  $V_R$ ?

# Summary of reverse bias

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- Reverse bias
  - Larger electric field
  - Wider depletion region
  - (Almost) no current flow
  - Variable capacitance

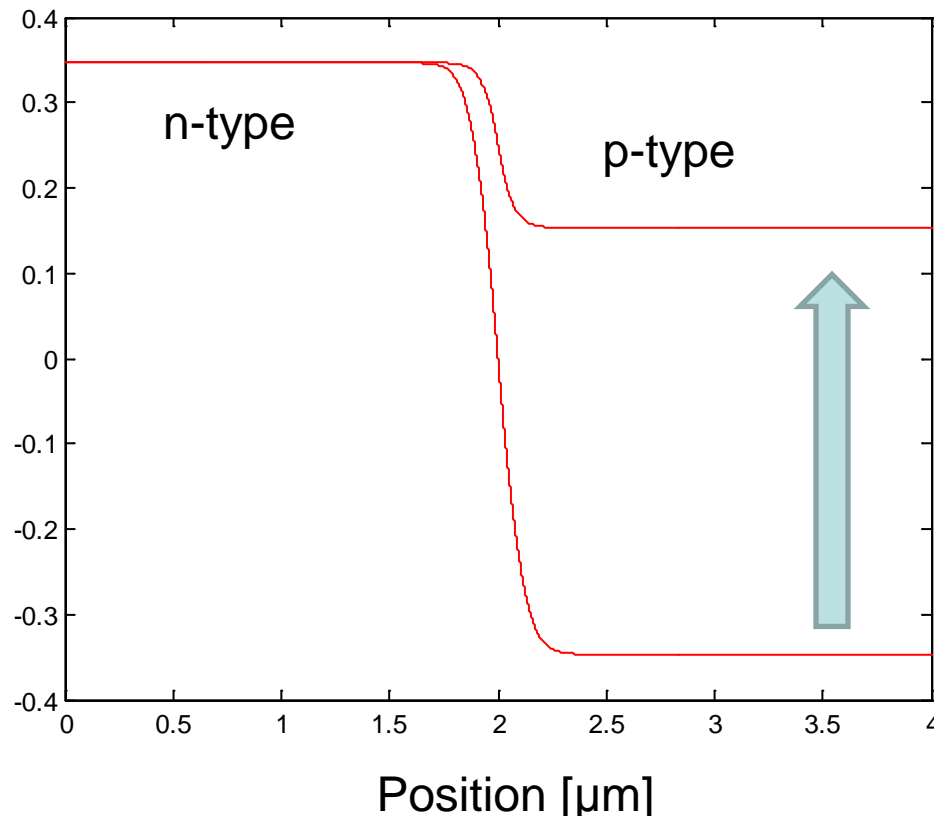


# Forward bias

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- Forward bias
  - We can easily guess that the depletion width will be reduced.
  - Potential barrier is lowered. (Equilibrium and 0.5 V)

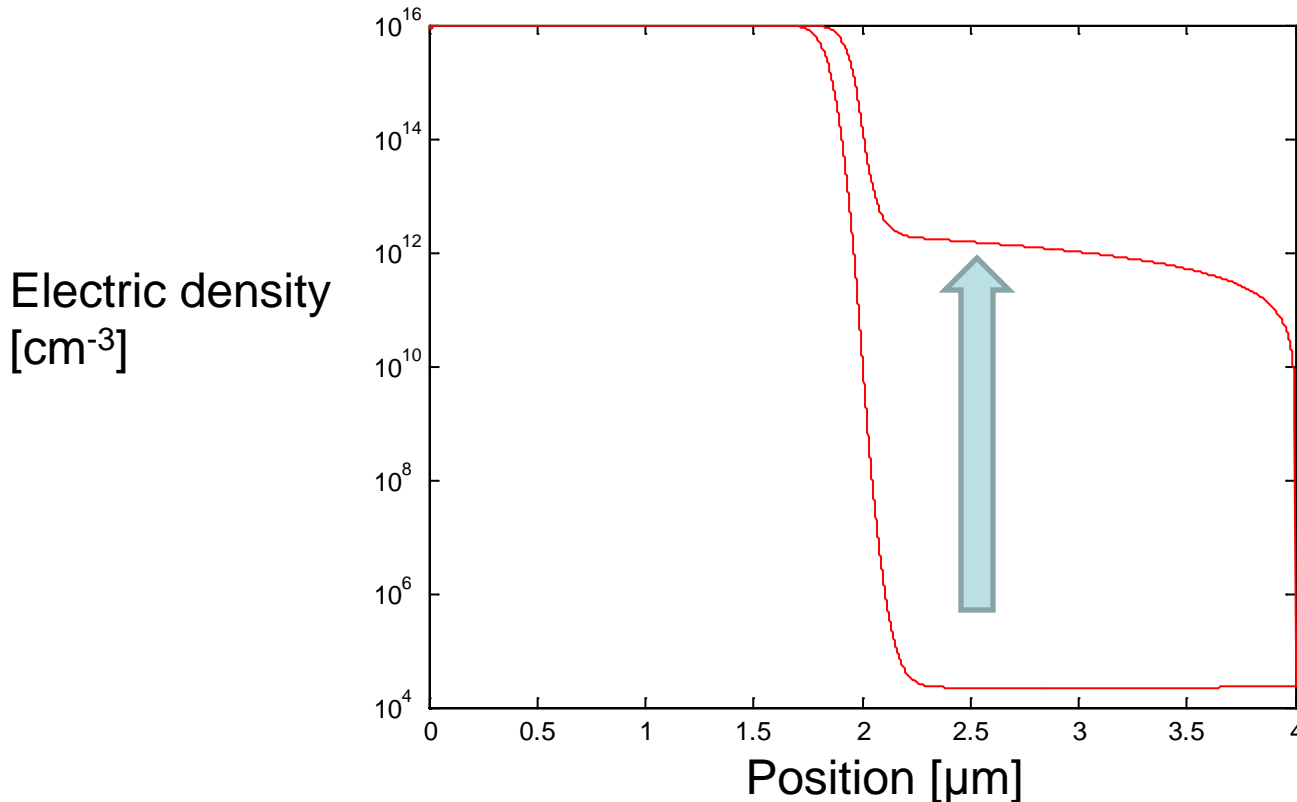
Electric potential  
[V]



# Density @ forward bias

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- Electron concentration (similar for hole concentration)
  - Equilibrium and 0.5 V
  - Exponential increase of electron density!



# IV characteristics

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- In forward bias,
  - The external voltage opposes the built-in potential, raising the diffusion currents substantially.
- In reverse bias,
  - The applied voltage enhances the field, prohibiting current flow.

$$I_D = I_S \left( \exp \frac{V_D}{V_T} - 1 \right)$$

- Here, the “reverse saturation current” is given by

$$I_S = Aq n_i^2 \left( \frac{D_n}{N_A L_n} + \frac{D_p}{N_D L_p} \right)$$

- $L_n$  and  $L_p$  are electron and hole “diffusion lengths,” respectively.

# An example

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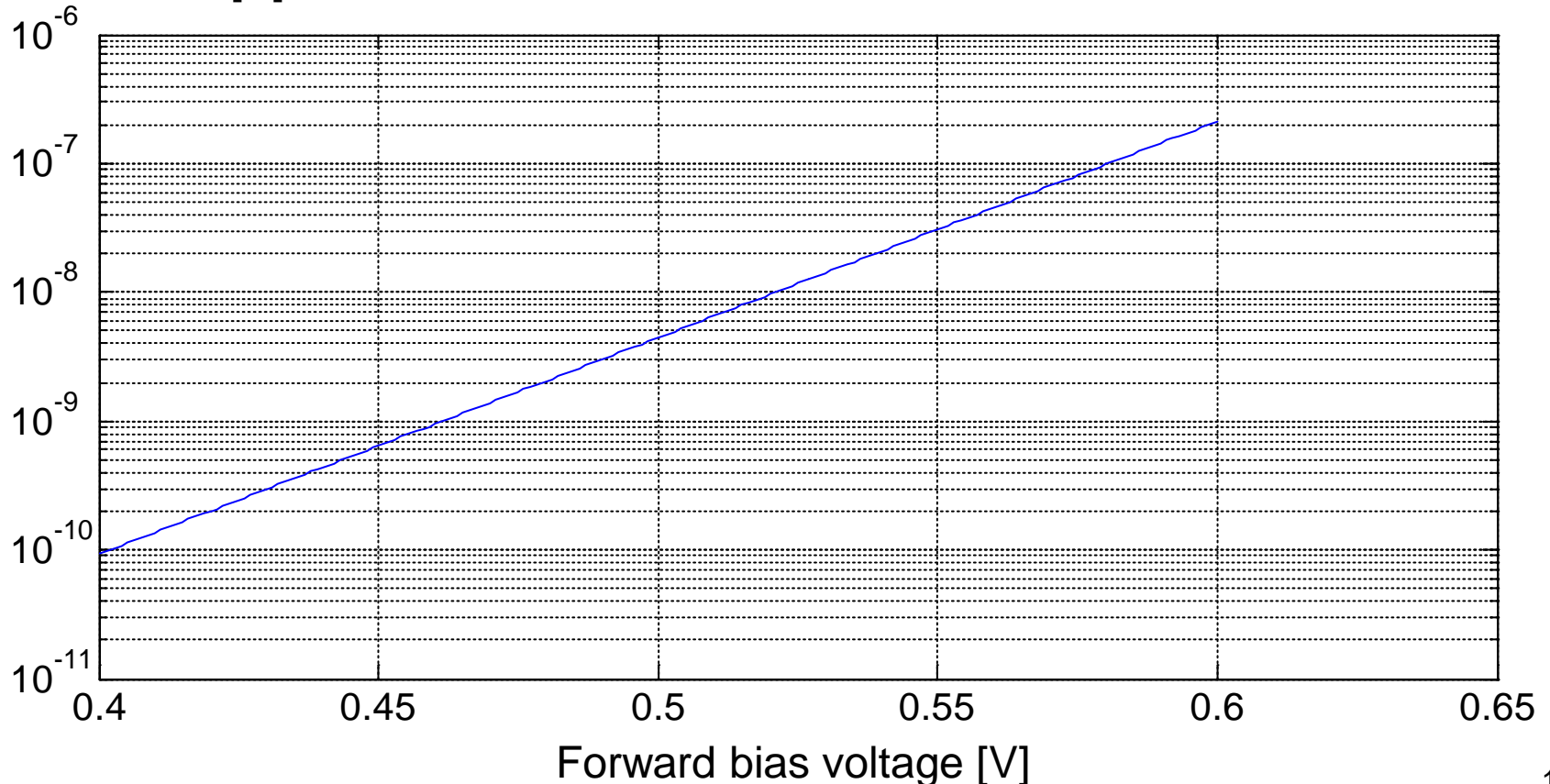
- Determine  $I_S$ .
  - The cross section of  $100 \mu\text{m}^2$
  - $L_n$  and  $L_p$  are  $20 \mu\text{m}$  and  $30 \mu\text{m}$ , respectively.
  - $L_n$  and  $L_p$  are  $20 \mu\text{m}$  and  $30 \mu\text{m}$ , respectively.
- When  $I_S = 1.77 \times 10^{-17} \text{ A}$ ,
  - Determine the forward bias current.
  - For  $V_D = 300 \text{ mV}$ ,  $I_S \left( \exp \frac{V_D}{V_T} - 1 \right) = 3.63 \text{ pA}$
  - For  $V_D = 800 \text{ mV}$ ,  $820 \mu\text{A}$

# 60 mV/dec, what is it?

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- Calculate  $V_T \ln 10$  at 300K.
  - Approximately 60 mV

Diode current [A]

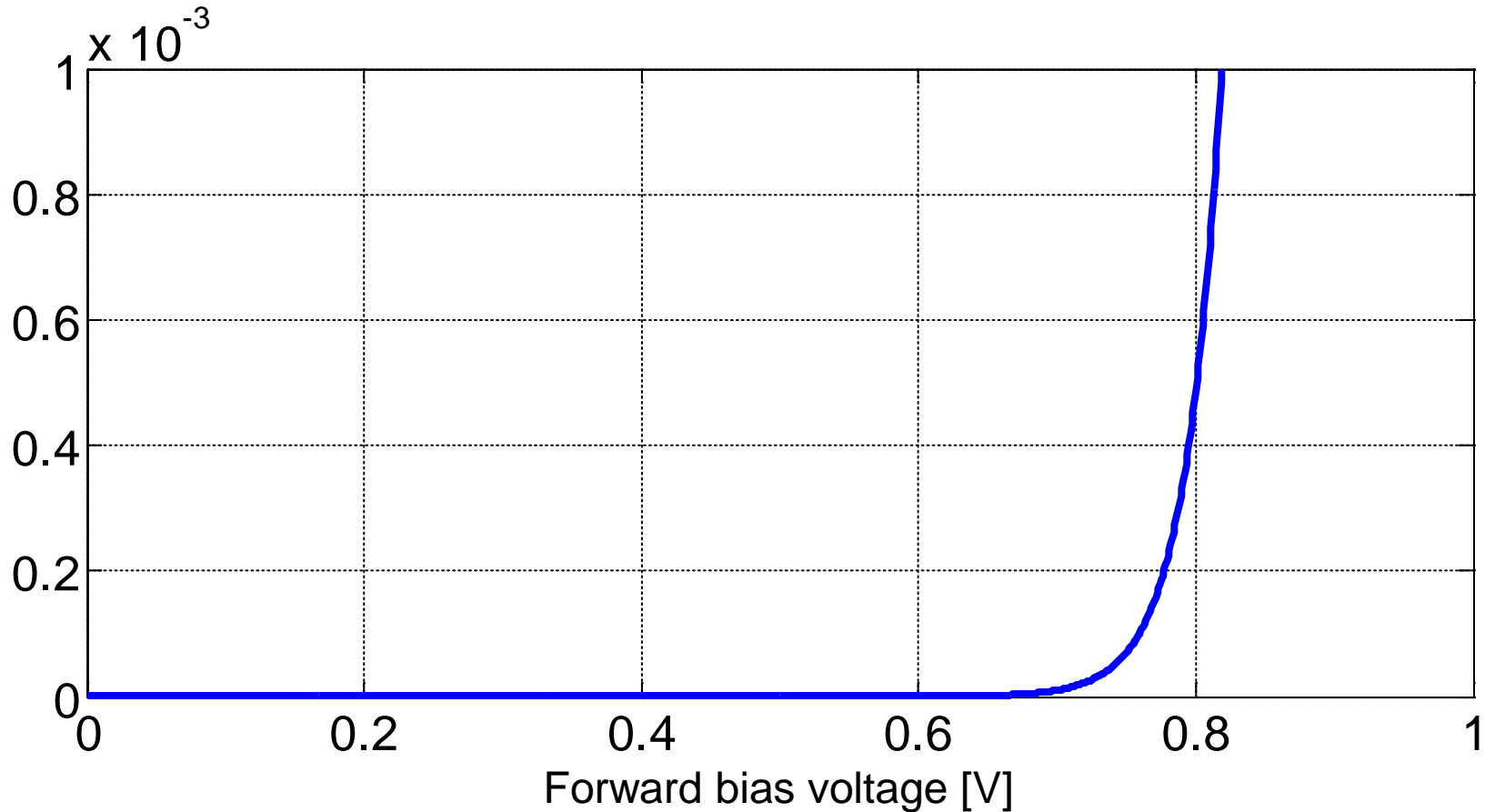


# Draw it!

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- In the linear scale, very steep increase of current!

Diode current [A]

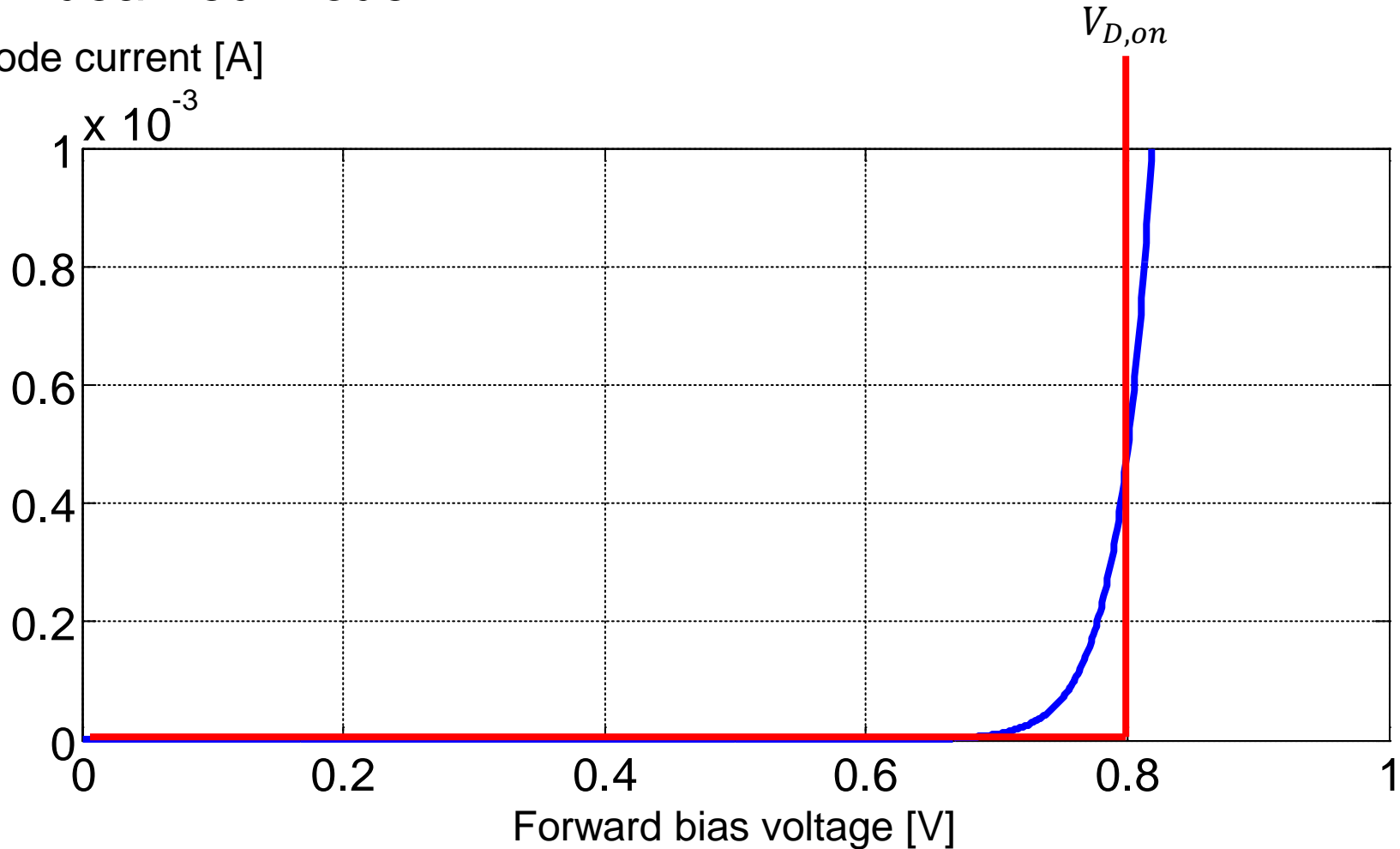


# Constant-voltage model

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- Idealized model

Diode current [A]

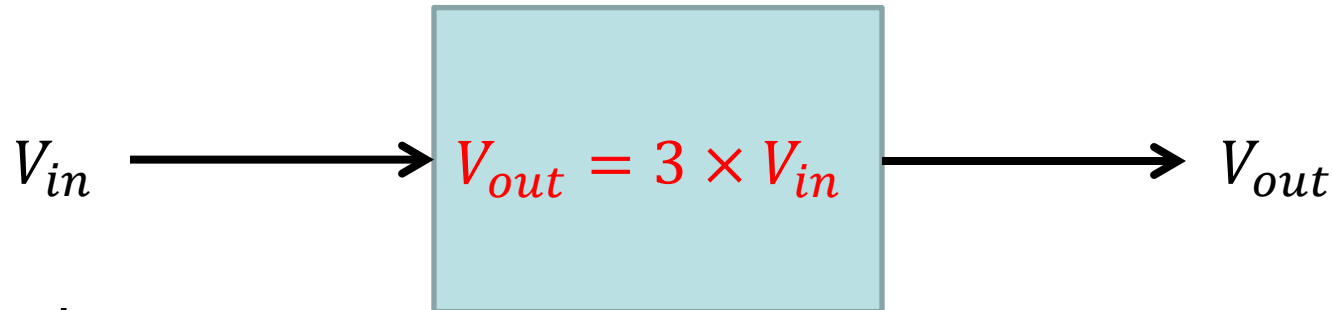


# A simple math

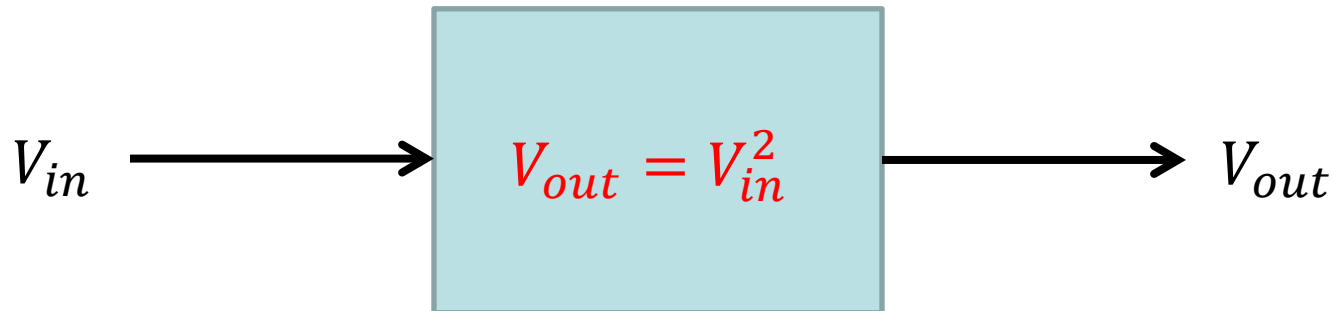
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- An input voltage,  $V_{in}(t) = \sin \omega t$

- A system



- Another system

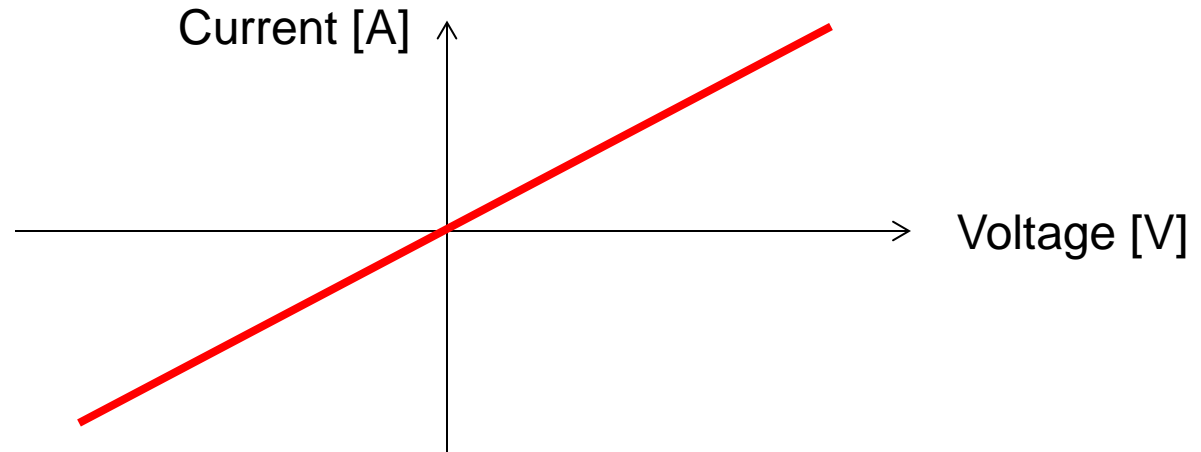




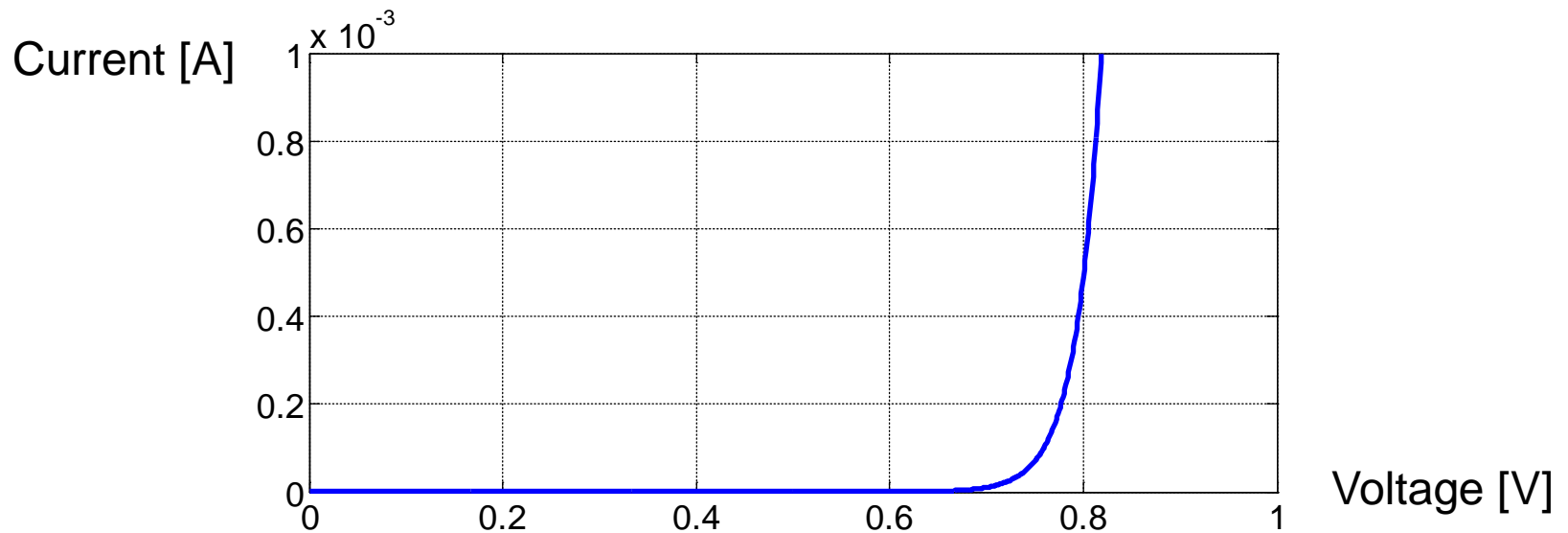
# Which is nonlinear?

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- A resistor



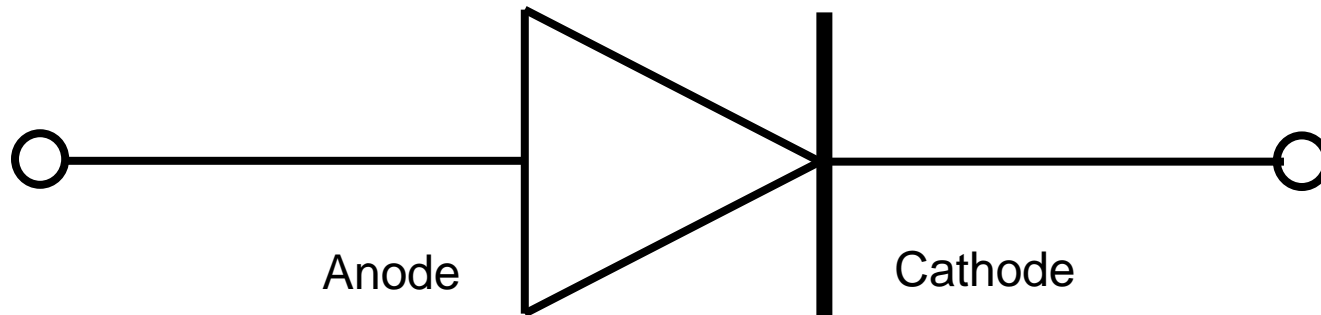
- A diode



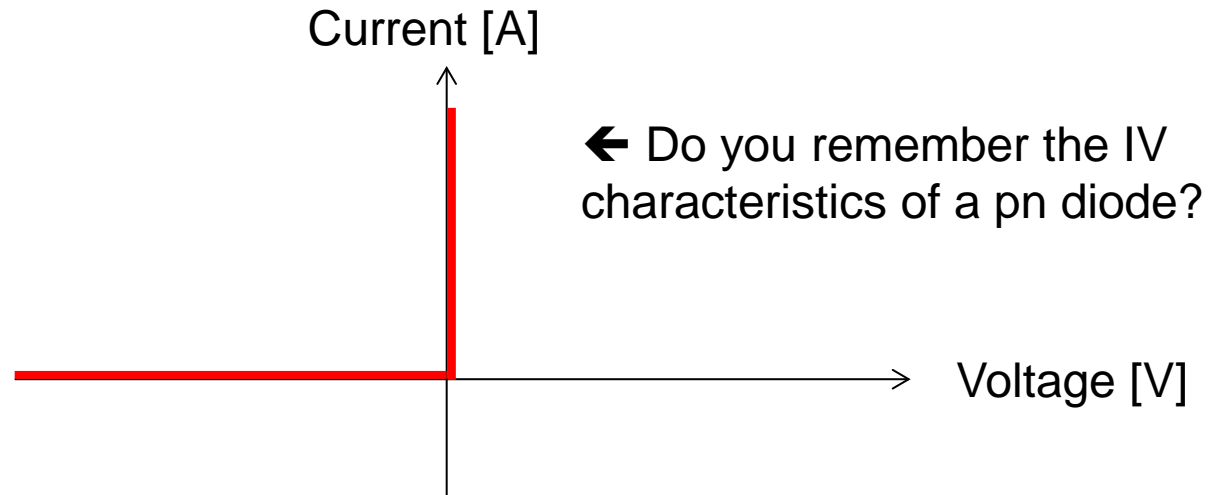
# Diode

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- Its symbol



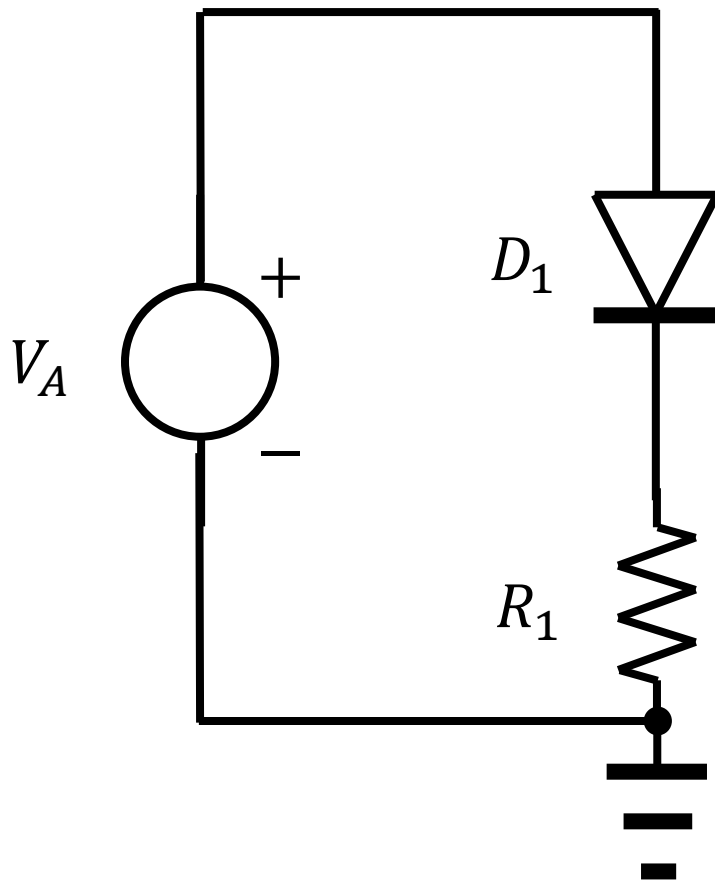
- Ideally, a perfect rectifier



# Example 3.4

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- A diode-resistor combination

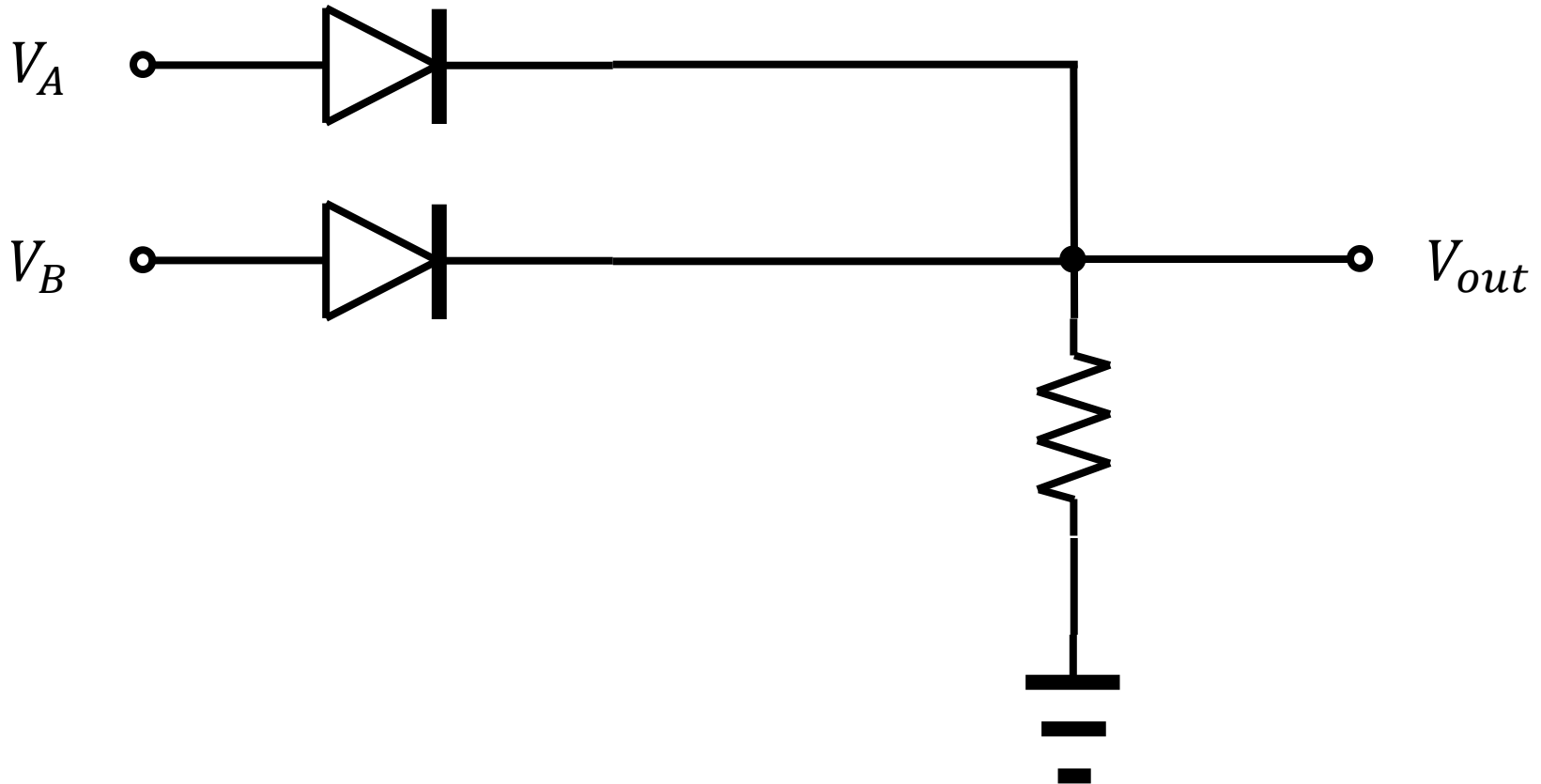


- ← Consider two cases,  $V_A > 0$  and  $V_A < 0$ .
- ← Draw the IV curve.

# Example 3.6

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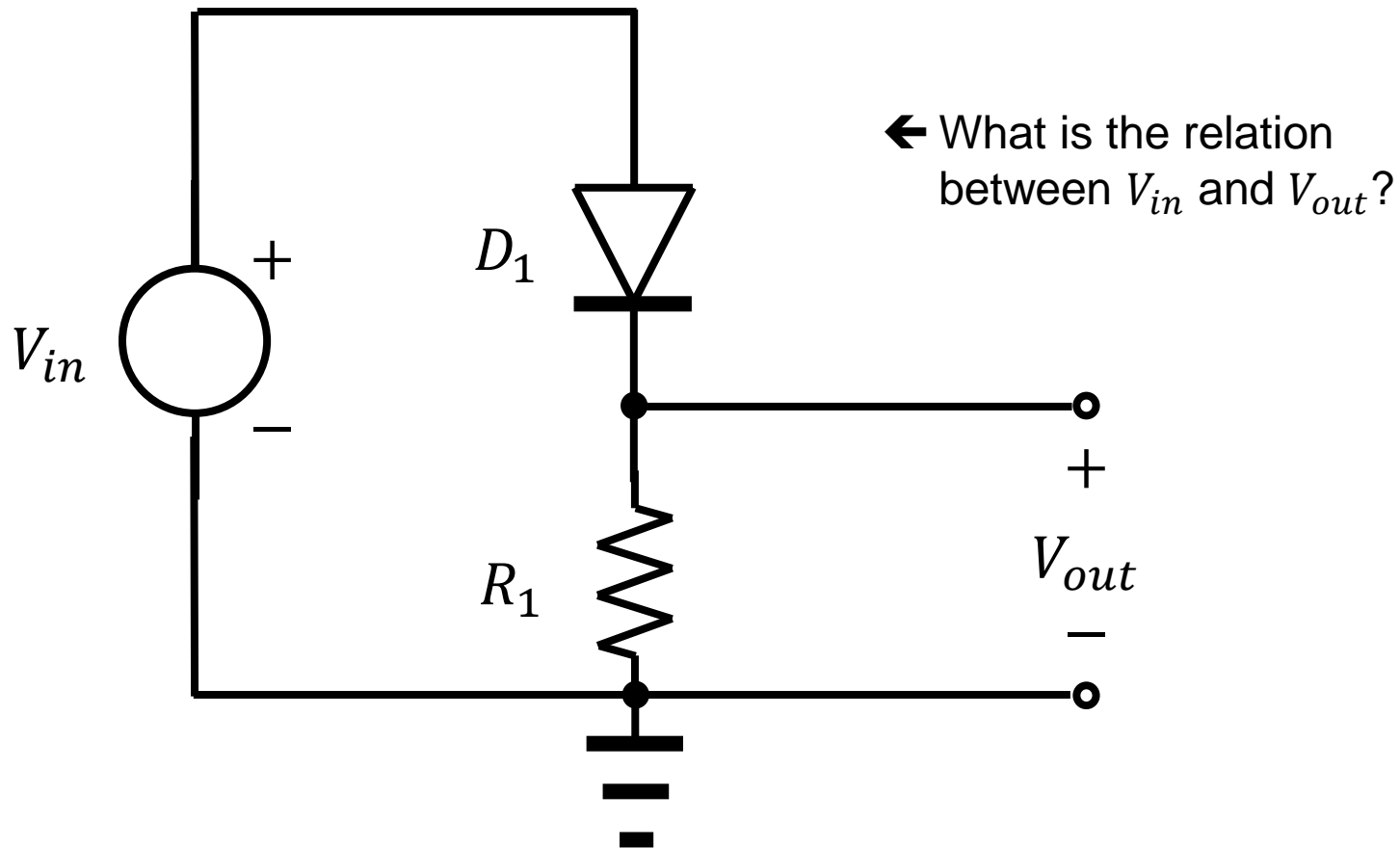
- An OR gate



# Rectifier

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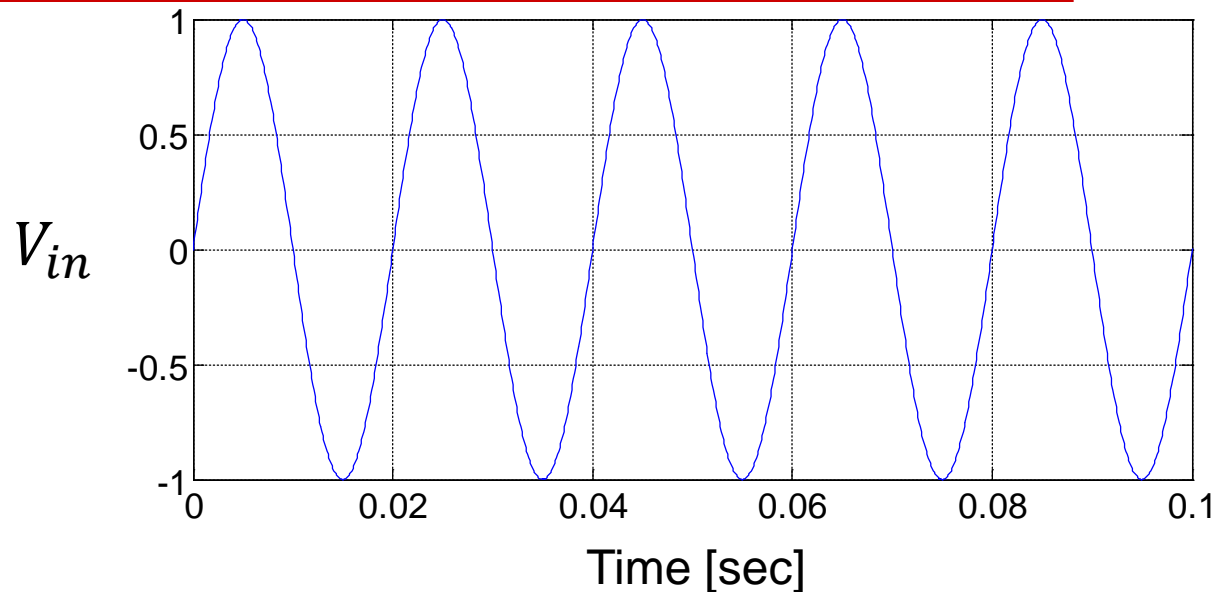
- Same circuit shown in Example 3.4.



# Input vs. output

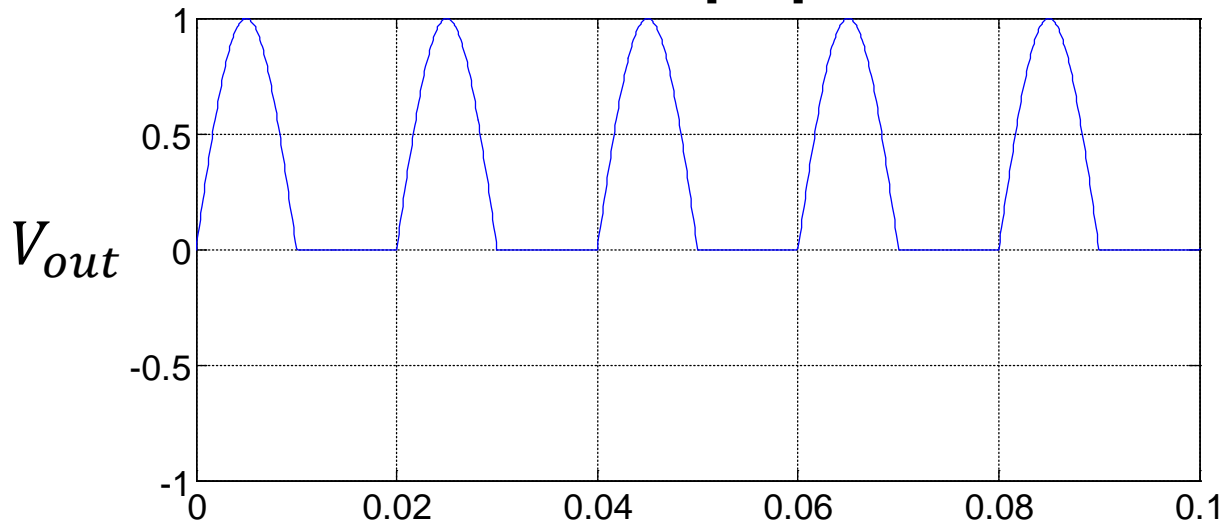
- Input

- 50 Hz
- Pure sine
- No dc



- Output

- 0, 50, 100, ... Hz
- dc voltage:  $\frac{1}{\pi}$  V

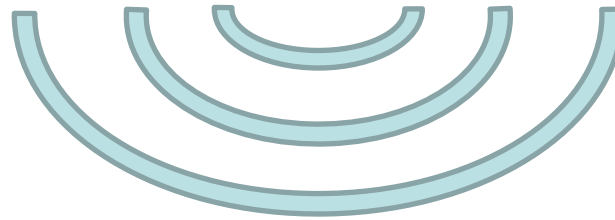


# Concept!

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- How to detect the electromagnetic radiation
  - Nonlinearity is required.

Incident THz wave (High freq)

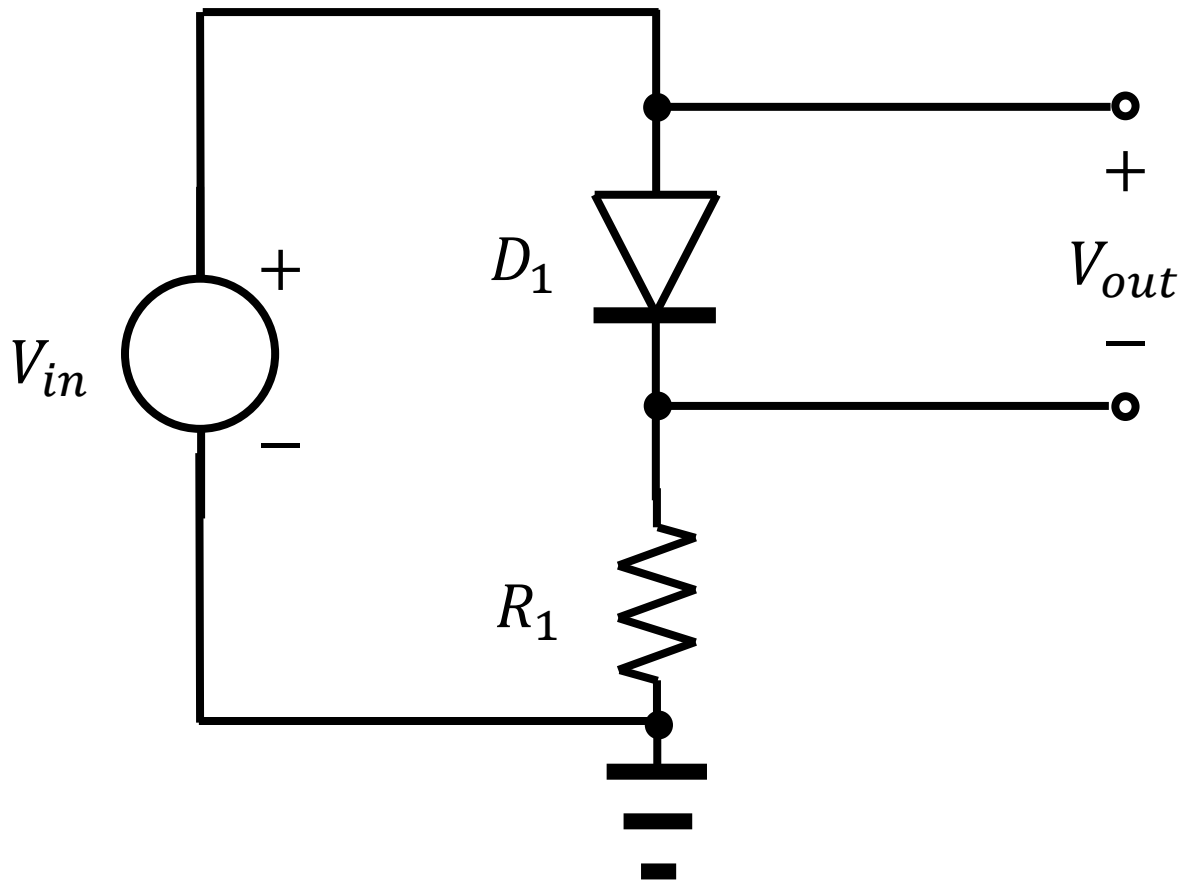


Output signal  
(Low freq)

# Rectifier, revisited

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- Same circuit shown in Example 3.4.





# pn junction as a diode

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- Exponential model

$$I_D = I_s \left( \exp \frac{V_D}{V_T} - 1 \right)$$

- Constant-voltage model
  - An “offset” voltage of  $V_{D,on}$

